

Title (en)

METHOD FOR DEPOSITING A SEMICONDUCTOR LAYER SYSTEM, WHICH CONTAINS GALLIUM AND INDIUM

Title (de)

VERFAHREN ZUM ABSCHIEDEN EINES HALBLEITER-SCHICHTSYSTEMS; WELCHES GALLIUM UND INDIUM ENTHÄLT

Title (fr)

PROCÉDÉ DE DÉPÔT D'UN SYSTÈME DE COUCHES SEMI-CONDUCTRICES CONTENANT DU GALLIUM ET DE L'INDIUM

Publication

EP 3966361 A1 20220316 (DE)

Application

EP 20725451 A 20200505

Priority

- DE 102019111598 A 20190506
- EP 2020062356 W 20200505

Abstract (en)

[origin: WO2020225228A1] The invention relates to a method for depositing a semiconductor layer system, wherein a first layer sequence has layers containing gallium and a second layer sequence has layers containing indium. In order to prevent gallium from being incorporated from residues in the process chamber into the layer containing indium when the layers containing indium are deposited, according to the invention a reactive gas containing indium is additionally supplied to the process chamber (2) during the first process step and the first process parameters (2) are adjusted such that the first layer or layer sequence (11) contains no indium or such that, in an intermediate step between the first and second process steps, a reactive gas containing indium is supplied to the process chamber (2) and in doing so the process parameters are adjusted such that no indium is deposited on the substrate (4), and, in the second process step, the second process parameters are adjusted such that the second layer contains no gallium.

IPC 8 full level

C23C 16/30 (2006.01); **C23C 16/44** (2006.01); **C23C 16/46** (2006.01); **C30B 25/10** (2006.01); **C30B 29/40** (2006.01)

CPC (source: EP KR US)

C23C 16/303 (2013.01 - EP KR US); **C23C 16/4401** (2013.01 - EP KR US); **C23C 16/45572** (2013.01 - US); **C23C 16/46** (2013.01 - EP KR US); **C30B 25/16** (2013.01 - EP KR); **C30B 29/403** (2013.01 - EP KR); **H01L 21/02458** (2013.01 - US); **H01L 21/0254** (2013.01 - US); **H01L 21/0262** (2013.01 - US); **H01L 29/66462** (2013.01 - US)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

WO 2020225228 A1 20201112; CN 114008239 A 20220201; CN 114008239 B 20240514; DE 102019111598 A1 20201112; EP 3966361 A1 20220316; JP 2022532055 A 20220713; JP 7547376 B2 20240909; KR 20220003542 A 20220110; TW 202106911 A 20210216; US 2022205086 A1 20220630

DOCDB simple family (application)

EP 2020062356 W 20200505; CN 202080044304 A 20200505; DE 102019111598 A 20190506; EP 20725451 A 20200505; JP 2021564981 A 20200505; KR 20217037090 A 20200505; TW 109114429 A 20200430; US 202017594996 A 20200505